4V Drive Pch MOSFET

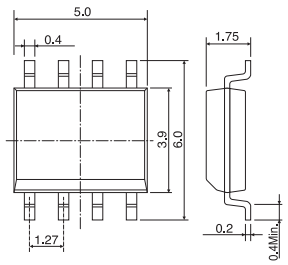
RRH100P03

●Structure
Silicon P-channel MOSFET

●Features
1) Low on-resistance.
2) Built-in G-S Protection Diode.
3) Small Surface Mount Package (SOP8).

●Application
Switching

●Dimensions (Unit : mm)
SOP8

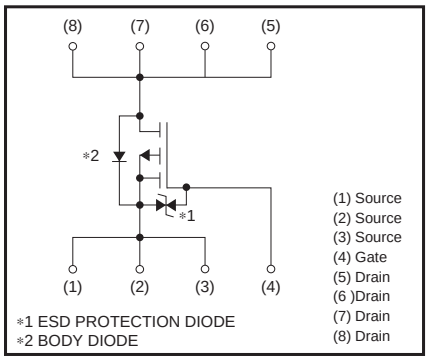


Each lead has same dimensions

●Packaging specifications

Type	Package	Taping
	Code	TB
	Basic ordering unit (pieces)	2500
RRH100P03		◯

●Inner circuit



●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	−30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±10	A
	Pulsed	I_{DP} ∗1	±40	A
Source current (Body Diode)	Continuous	I_S	−1.6	A
	Pulsed	I_{SP} ∗1	−40	A
Power dissipation		P_D ∗2	2.0	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

∗1 Pw≤10μs, Duty cycle≤1%
∗2 Mounted on a ceramic board.

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)∗	62.5	°C / W

∗ Mounted on a ceramic board.

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●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	V_{GS}=±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	–30	–	–	V	I_D=–1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	–1	μA	V_{DS}=–30V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	–1.0	–	–2.5	V	V_{DS}=–10V, I_D=–1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	–	9.0	12.6	mΩ	I_D=–10A, V_{GS}=–10V
		–	12.5	17.5		I_D=–5A, V_{GS}=–4.5V
		–	14.0	19.6		I_D=–5A, V_{GS}=–4.0V
Forward transfer admittance	$\|Y_{fs}\|$*	13	–	–	S	I_D=–10A, V_{DS}=–10V
Input capacitance	C_{iss}	–	3600	–	pF	V_{DS}=–10V
Output capacitance	C_{oss}	–	450	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	450	–	pF	f=1MHz
Turn-on delay time	$t_{d(on)}$ *	–	25	–	ns	I_D=–5A, V_{DD} ≒ –15V
Rise time	t_r *	–	60	–	ns	V_{GS}=–10V
Turn-off delay time	$t_{d(off)}$ *	–	150	–	ns	R_L=3.0Ω
Fall time	t_f *	–	100	–	ns	R_G=10Ω
Total gate charge	Q_g *	–	39	–	nC	I_D=–10A, V_{DD} ≒ –15V V_{GS}=–5V R_L=1.5Ω R_G=10Ω
Gate-source charge	Q_{gs} *	–	8.5	–	nC	
Gate-drain charge	Q_{gd} *	–	13.5	–	nC	

*Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward Voltage	V_{SD} *	–	–	–1.2	V	I_S=–10A, V_{GS}=0V

*Pulsed

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●Electrical characteristics curves

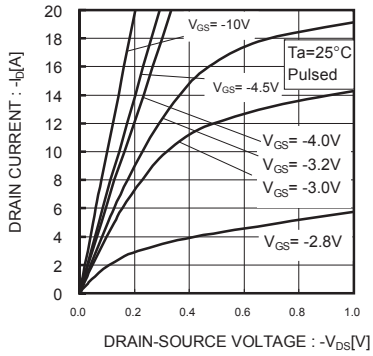

Fig.1 Typical output characteristic(I)

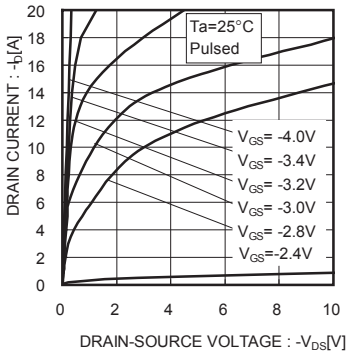

Fig.2 Typical output characteristics(Ⅱ)

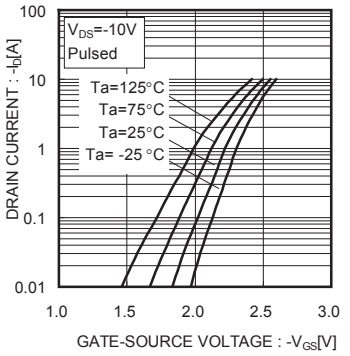

Fig.3 Typical Transfer Characteristics

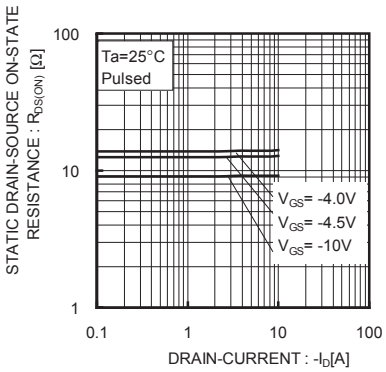

Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(Ⅰ)

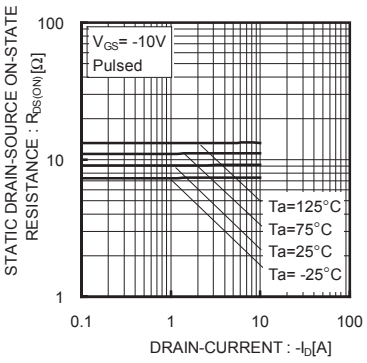

Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(Ⅱ)

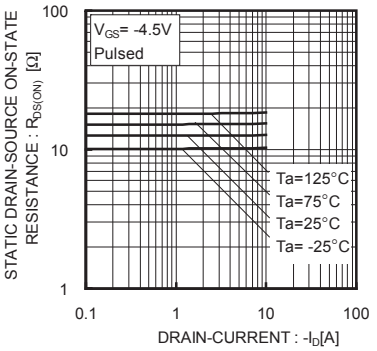

Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)

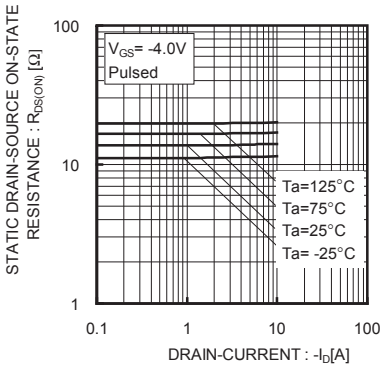

Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(Ⅳ)

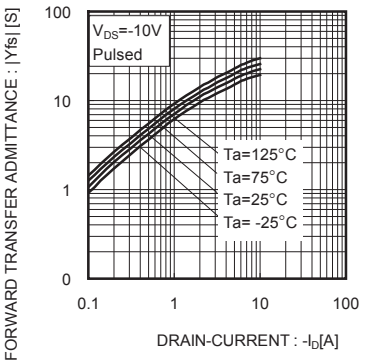

Fig.8 Forward Transfer Admittance vs. Drain Current

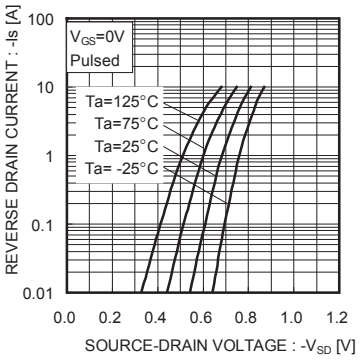

Fig.9 Reverse Drain Current vs. Sourse-Drain Voltage

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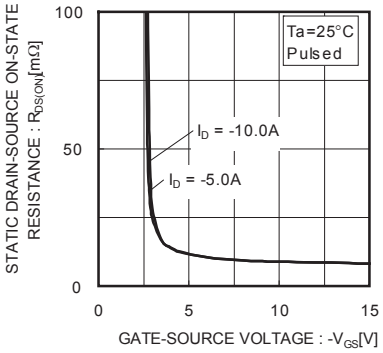

Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

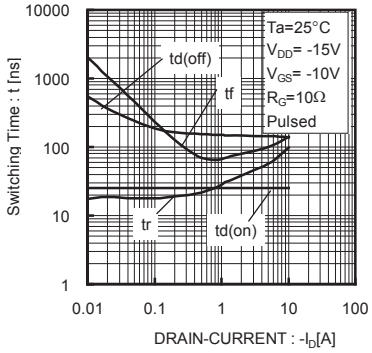

Fig.11 Switching Characteristics

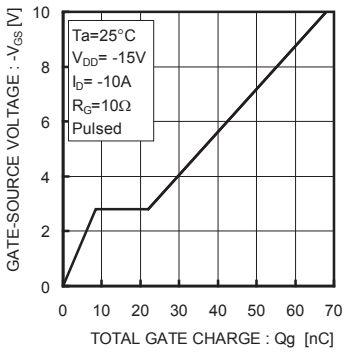

Fig.12 Dynamic Input Characteristics

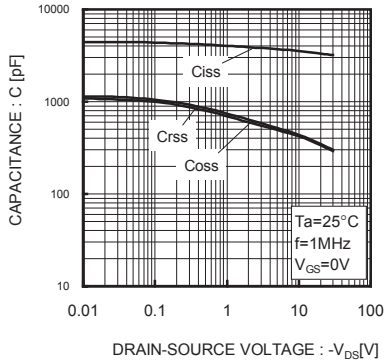

Fig.13 Typical Capacitance vs. Drain-Source Voltage

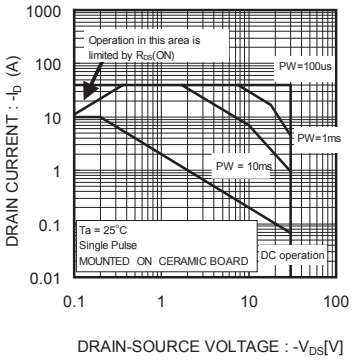

Fig.14 Maximum Safe Operating Aera

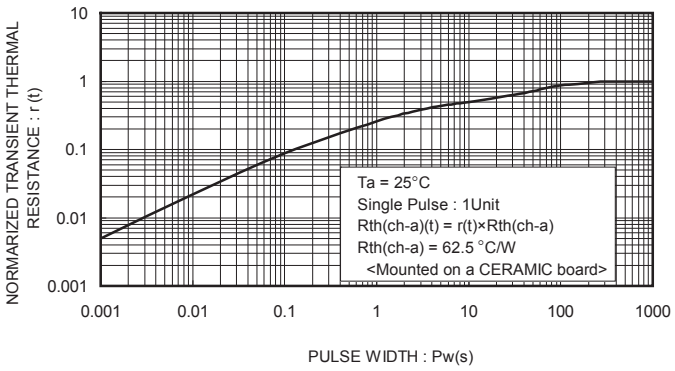

Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

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●**Measurement circuit**

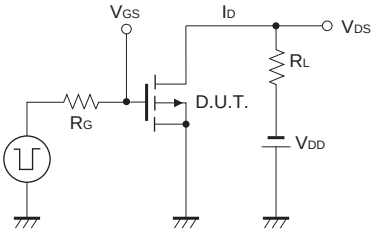

Fig.1-1 Switching Time Measurement Circuit

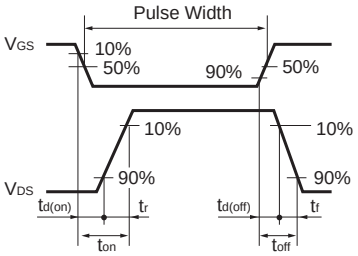

Fig.1-2 Switching Waveforms

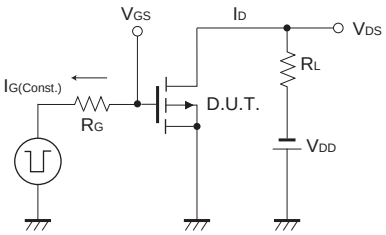

Fig.2-1 Gate Charge Measurement Circuit

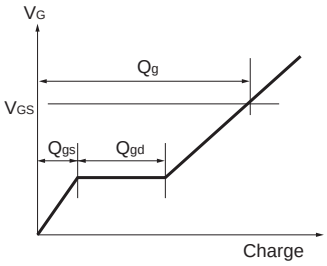

Fig.2-2 Gate Charge Waveform

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